INFORMATION DISCLOSURE STATEMENT

Applicant	:	Gonzalez, et al.
App. No	:	10/661,414
Filed	:	September 12, 2003
For	:	MULTIPLE THICKNESS GATE DIELECTRIC LAYERS
Examiner	:	Fetsum Abraham
Art Unit	:	2826

CERTIFICATE OF MAILING

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first-class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

March 18, 2005
(Date)

Michael S. Okamoto, Reg. No. 47,831

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO/SB/08 Equivalent listing nine (9) references that are of record in U.S. Patent Application No. 09/879,604, filed June 12, 2001, which is the parent of this continuation application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. These same references were also cited in an IDS filed with the present application on September 12, 2003 that enclosed the PTO-892 form from the parent application. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d)(1).

This Information Disclosure Statement is being filed after the mailing date of a Notice of Allowance under § 1.311. However, no new art is disclosed herein, and thus, Applicants believe that no additional fees are due. The listed art in enclosed form PTO/SB/08 should have already been considered by the Examiner in accordance with M.P.E.P. § 609(I)(A)(2), which states that "[t]he examiner will consider information which has been considered by the Office in a parent application when examining (A) a continuation application..."

PTO/SB/08 Equivalent

INFORMATION DISCLOSURE STATEMENT BY APPLICANT		
	Application No.	10/661,414
	Filing Date	September 12, 2003
	First Named Inventor	Gonzalez
	Art Unit	2826
(Multiple sheets used when necessary)	Examiner	Fetsum Abraham
SHEET 1 OF 1	Attorney Docket No.	MICRON.079DV1C1

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number *Number - Kind Code (if known)* Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
		5,101,251	03-31-1992	Wakamiya, et al.	
		5,395,786	03-07-1995	Hsu, et al.	
		5,658,811	08-19-1997	Kimura, et al.	
		5,668,035	09-16-1997	Fang, et al.	
		5,731,238	03-24-1998	Cavins, et al.	
		5,843,817	12-01-1998	Lee, et al.	
		5,960,289	09-28-1999	Tsui, et al.	
		6,136,728	10-24-2000	Wang	

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Foreign Patent Document *Country Code-Number-Kind Code* Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T^1

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T^1
		Sekine et al., "Self-aligned tungsten strapped source/drain and gate technology realizing the lowest sheet resistance for sub-quarter micron CMOS," International Electron Devices Meeting, December 1994, IEEE, p. 493-496	

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Examiner Signature	Date Considered

***Examiner:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

T^1 - Place a check mark in this area when an English language Translation is attached.